

CORRIGENDUM

Dislocation Mobilities in GaN from Molecular Dynamics Simulations– CORRIGENDUM

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The original Figure 4 published in this paper is incorrect. Below is the correct figure, as well as updates to the surrounding text regarding this figure:

Page 3, in section “c-type edge dislocations”:

There are two slip systems for c-type dislocations, $\{\bar{1}\bar{1}20\}\{0001\}$ and $\{\bar{1}\bar{1}00\}\{0001\}$.

Page 4:

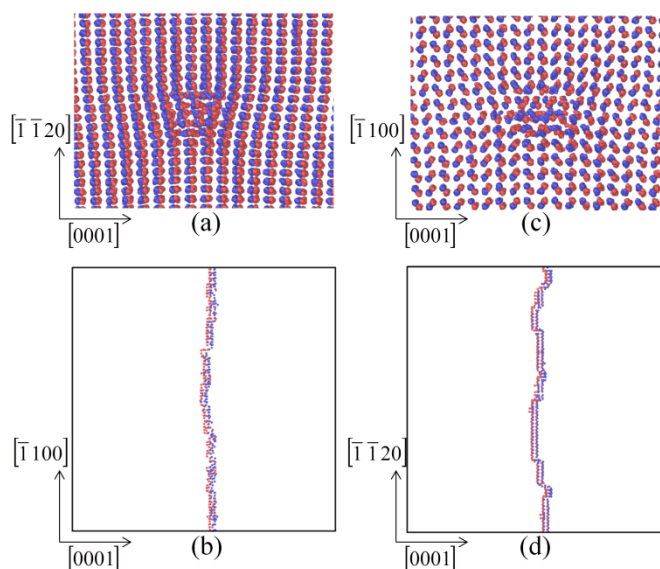


Figure 4 – (a) The core structure of a $(\bar{1}\bar{1}20)[0001]$ c-type dislocation, (b) the same dislocation looking down on the glide plane, with crystallographic directions as indicated. (c) and (d) are the same for a $(\bar{1}\bar{1}00)[0001]$ c-type dislocation.

The author regrets this error.

Reference

N. Scott Weingarten (2015). Dislocation Mobilities in GaN from Molecular Dynamics Simulations. *MRS Proceedings*, 1741, mrsf14-1741-aa01-03, doi:10.1557/opl.2015.25.